

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: : Yong-Bae Kim and Philippe Schoenborn

Appl. No. : Continuation of 09/898,194

Filed: : Herewith

Title : PROCESS FOR REMOVAL OF PHOTORESIST MASK USED FOR  
MAKING VIAS IN LOW K CARBON-DOPED SILICON OXIDE  
DIELECTRIC MATERIAL, AND FOR REMOVAL OF ETCH  
RESIDUES FROM FORMATION OF VIAS AND REMOVAL OF  
PHOTORESIST MASK

Grp./ A.U. : 1765

Examiner : Kin-Chan Chen

Docket No. : 01-125/1C

**PRELIMINARY AMENDMENT**

Honorable Commissioner for Patents  
Post Office Box 1450  
Alexandria, VA 22313-1450

**Date:** July 14, 2003

Sir:

Please amend the accompanying continuation application as follows: